# BAV99WT1, SBAV99WT1G, BAV99RWT1, SBAV99RWT1G

# Dual Series Switching Diodes

The BAV99WT1 is a smaller package, equivalent to the BAV99LT1.

### Features

- These Devices are Pb-Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable

### **Suggested Applications**

- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

#### MAXIMUM RATINGS (Each Diode)

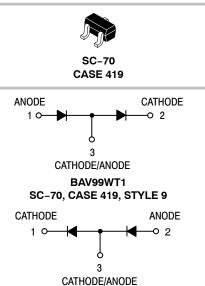
Rating	Symbol	Value	Unit	
Reverse Voltage	V <sub>R</sub>	100	Vdc	
Forward Current	١ <sub>F</sub>	215	mAdc	
Peak Forward Surge Current	I <sub>FM(surge)</sub>	500	mAdc	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	70	V	
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	I <sub>F(AV)</sub>	715	mA	
Repetitive Peak Forward Current	I <sub>FRM</sub>	450	mA	
Non-Repetitive Peak Forward Current $t = 1.0 \ \mu s$ $t = 1.0 \ ms$ $t = 1.0 \ s$	I <sub>FSM</sub>	2.0 1.0 0.5	A	

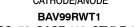
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

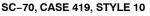


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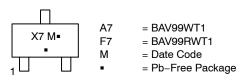
http://onsemi.com











#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BAV99WT1G	SC–70 (Pb–Free)	3,000 / Tape & Reel
SBAV99WT1G	SC–70 (Pb–Free)	3,000 / Tape & Reel
BAV99RWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SBAV99RWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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#### THERMAL CHARACTERISTICS

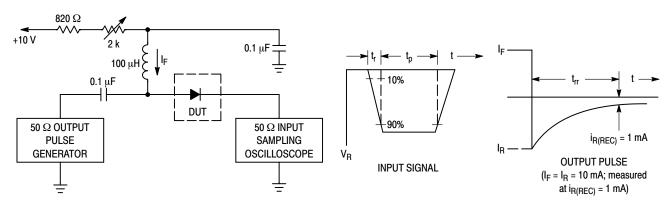
Characteristic	Symbol	Мах	Unit
Total Device Dissipation FR-5 Board, (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	200 1.6	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	625	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ hetaJA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

#### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			•
Reverse Breakdown Voltage (I <sub>(BR)</sub> = 100 μA)	V <sub>(BR)</sub>	100	_	Vdc
Reverse Voltage Leakage Current ( $V_R = 100 \text{ Vdc}$ ) ( $V_R = 25 \text{ Vdc}, T_J = 150^{\circ}\text{C}$ ) ( $V_R = 70 \text{ Vdc}, T_J = 150^{\circ}\text{C}$ )	I <sub>R</sub>	- - -	2.5 30 50	μAdc
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz)	C <sub>D</sub>	_	1.5	pF
Forward Voltage $(I_F = 1.0 \text{ mAdc})$ $(I_F = 10 \text{ mAdc})$ $(I_F = 50 \text{ mAdc})$ $(I_F = 150 \text{ mAdc})$	V <sub>F</sub>	- - - -	715 855 1000 1250	mVdc
Reverse Recovery Time (I <sub>F</sub> = I <sub>R</sub> = 10 mAdc, $i_{R(REC)}$ = 1.0 mAdc) (Figure 1) R <sub>L</sub> = 100 $\Omega$	t <sub>rr</sub>	_	6.0	ns
Forward Recovery Voltage (I <sub>F</sub> = 10 mA, t <sub>r</sub> = 20 ns)		_	1.75	V

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.



Notes: (a) A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA. (b) Input pulse is adjusted so I<sub>R(peak)</sub> is equal to 10 mA. (c) t<sub>p</sub> » t<sub>rr</sub>

#### Figure 1. Recovery Time Equivalent Test Circuit

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### CURVES APPLICABLE TO EACH DIODE

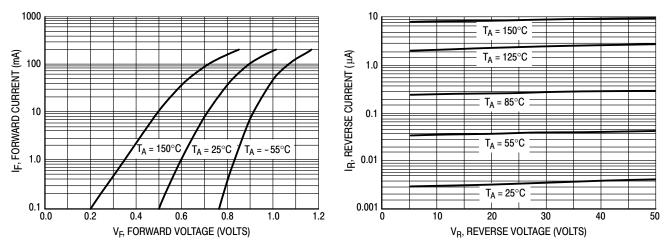


Figure 2. Forward Voltage

Figure 3. Leakage Current

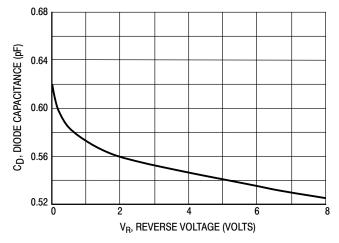
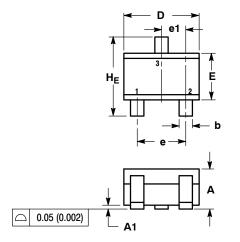


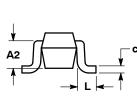
Figure 4. Capacitance

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#### PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE N





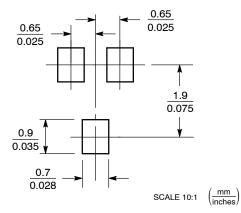
NOTES:

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH. 1.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Е	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
Г	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 9: PIN 1. ANODE CATHODE 2 3 CATHODE-ANODE STYLE 10: PIN 1. CATHODE ANODE 2. 3 ANODE-CATHODE

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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